## JAYPEE UNIVERSITY OF INFORMATION TECHNOLOGY, WAKNAGHAT MAKEUP EXAMINATION- 2016

## **B.Tech IV Semester**

**COURSE CODE: 10B11EC411** 

MAX. MARKS: 25

COURSE NAME: Semiconductor Devices (A. 1994)

COURSE CREDITS: 04

MAX. TIME: 1Hr 30 Min

Note: All questions are compulsory. Carrying of mobile phone during examinations will be treated as case of unfair means.

Q1. (a). What is ment by low level injection?

[5x1]

- (b). What is the need of Doping?
- (c). Show the temperature dependency of mobility through graph.
- (d). What is the effect of reverse bias on the width of the depletion region of a P-N junction?
- (e). Define mean life-time of a carrier.
- Q2. (a) Show that the physical characteristics of the transition capacitance are similar to the parallel-plate capacitor and prove that  $C_T = \frac{A\varepsilon}{W}$ , where A is the cross-sectional area of the diode and W is the width of the depletion layer.
  - (b) Which diode capacitance is significant in the forward direction and which one is significant in the reverse direction? Plot the variation of the capacitance with forward bias and reverse bias. [2]
- Q3. (a) Derive the diffusion equation for holes from the equation of continuity and find out its solution.
  - solution. [3]
    (b) The depletion region extends deeper into the lightly doped (N) region of the diode.
    Explain why? [2]
- Q4. A PN<sup>+</sup> Si junction diode is doped with  $N_D = 10^{16}/\text{cm}^3$  and  $N_A = 10^{15}/\text{cm}^3$ . Determine the location of Fermi levels With respect to the bottom of the conduction band on each side of the junction. Draw the energy band diagram. For Si,  $n_i = 10^{10}/\text{cm}^3$ .
  - (b) Explain the movement of energy bands (with diagram)
    - (i) When diode is forward biased? (ii) When diode is reversed biased?
  - (c) How does an increase of diode reverse-bias increase the diode reverse current?

Q5.Maximum value of electric field is given by:

[5]

$$E_{\theta} = \frac{-qN_{a}X_{po}}{\varepsilon} = \frac{-qN_{d}X_{no}}{\varepsilon}$$
Prove that: 
$$W = \sqrt{\frac{2\varepsilon Vo}{q} \frac{N\alpha + Nd}{N\alpha Nd}}$$